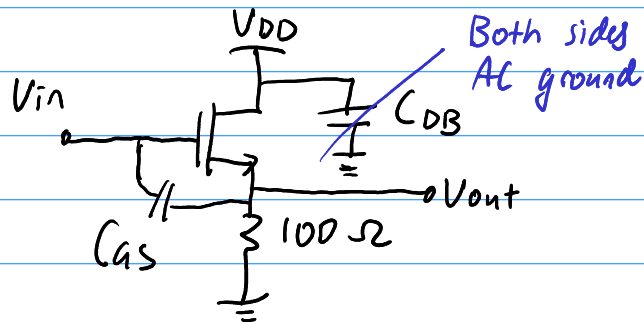


11.57

NMOS source follower must drive 100Ω with $A_v = 0.8$. Given $I_D = 1 \text{ mA}$, $\mu_n C_{ox} = 100 \text{ } \mu\text{A/V}^2$, $C_{ox} = 12 \text{ fF}/\mu\text{m}^2$, $L = 0.18 \text{ } \mu\text{m}$, $\lambda = 0$, $C_{GD} \approx 0$, $C_{SB} \approx 0$, $C_{GS} = \frac{2}{3} W L C_{ox}$. Find input capacitance.



Bias network not shown.

First find the required g_m . Recall that the gain of a source follower is

$$A_v = \frac{R_s}{\frac{1}{g_m} + R_s} \Rightarrow \frac{1}{g_m} = \frac{R_s}{A_v} - R_s$$

$$\frac{1}{g_m} = \frac{100}{0.8} - 100 = 25 \Omega.$$

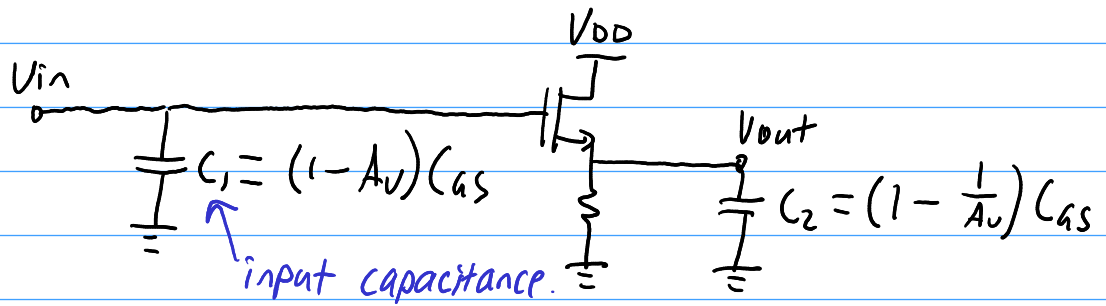
$$g_m = 40 \text{ mS}.$$

Since g_m and I_D are fixed, we can solve for $\frac{W}{L}$.

$$g_m = \sqrt{2 \mu_n C_{ox} \frac{W}{L} I_D}$$
$$(0.04)^2 = 2 \times 100 \times 10^{-6} \times W \times \frac{1}{0.18 \times 10^{-6}} \times 0.001$$

$$W = 1.44 \text{ mm.} \quad \leftarrow \text{Big value, for a real design increase } I_D \text{ to reduce } \frac{W}{L}.$$

Use Miller approx. to convert C_{GS} .



$$\begin{aligned}
 C_{gs} &= \frac{2}{3} WL C_{ox} \\
 &= \frac{2}{3} \times 1.44 \times 10^{-3} \times 0.18 \times 10^{-6} \times 12 \times \frac{10^{-15}}{(10^{-6})^2} \\
 &= 2.07 \text{ pF.}
 \end{aligned}$$

$$\begin{aligned}
 \therefore C_1 &= (1 - 0.8) C_{gs} \\
 &= 415 \text{ fF.}
 \end{aligned}$$

Notice higher I_D would reduce W & therefore reduce the input capacitance.